c) Amendments to the Claims

Please cancel claims 12-27, 35-38 and 45-55 without prejudice or disclaimer. Please amend claims 9 and 39. A detailed listing of all the claims that are or were on the application is provided.

--1. (Original) An exhaust processing process of a processing apparatus for processing a substrate or a film, comprising the steps of: after processing a substrate or a film, introducing a non-reacted gas and/or a by-product into a trap means having therein a filament comprising a high-melting metal material comprising as a main component at least one of tungsten, molybdenum and rhenium; and processing the non-reacted gas and/or the by-product inside the trap means.

2. (Original) The exhaust processing process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film on the substrate by a plasma CVD process.

3. (Original) The exhaust processing process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film on the substrate by a thermal CVD process.

4. (Original) The exhaust processing process according to claim 1, wherein the processing apparatus is an apparatus for forming a deposited film on the substrate by a photo CVD process.

5. (Original) The exhaust processing process according to claim 1, wherein the processing apparatus is an apparatus for processing the film by a dry etching process.

6. (Original) The exhaust processing process according to claim 1, wherein the temperature of the filament is 500°C or more.

7. (Original) The exhaust processing process according to claim 1, wherein the temperature of the filament is 1400°C or more.

8. (Original) The exhaust processing process according to claim 1, wherein the configuration of the filament comprises a single linear shape, a plurality of linear shapes or a linear shape wound in spirals.

9. (Currently Amended) The exhaust processing process according to claim 1, wherein the film is a deposited film comprising a silicon-based amorphous or silicon-based microcrystalline ~~mycrocrystalline~~ material.

10. (Original) The exhaust processing process according to claim 1, wherein the non-reacted gas and/or the by-product comprises silicon or a compound thereof as a main component.

11. (Original) The exhaust processing process according to claim 1, wherein a wall surface of the trap is of a double structure, and an inner wall surface is detachable.

Claims 12-27 (Cancelled)

28. (Original) A process of processing an exhaust gas exhausted from a processing space for processing a substrate or a film therein, which comprises exhausting the exhaust gas so as to be in contact with a heat generating member provided in an outlet of the processing space and controlled so as to have a current density within the range of 5 to 500 A/mm^2, whereby a chemical reaction is caused in a non-reacted gas and/or a by-product contained in the exhaust gas.

29. (Original) The exhaust gas processing process according to claim 28, wherein the processing process of the substrate or the film is a plasma CVD process.

30. (Original) The exhaust gas processing process according to claim 28, wherein when a power supply to the heat generating member is started, an applied current density is gradually raised.

31. (Original) The exhaust gas processing process according to claim 28, wherein when a power supply to the heat generating member is stopped, an applied current density is gradually lowered.

32. (Original) The exhaust gas processing process according to claim 28, wherein during a power supply to the heat generating member, a predetermined current density is controlled to be constant.

33. (Original) The exhaust gas processing process according to claim 28, wherein the heat generating member is used in plurality, and wherein at least one heat generating member is controlled with a current density distribution which is different by at least 10 A/mm^2 from that of the other heat generating members.

34. (Original) The exhaust gas processing process according to claim 28, wherein the heat generating member comprises tungsten.

Claims 35-38 (Cancelled)

39. (Currently Amended) A plasma processing process which uses a plasma processing apparatus having a processing chamber for plasma-processing a substrate or a film and an exhaust means for exhausting a gas from the processing chamber, the process comprising: using a chemical reaction causing means provided in an exhaust pipe connecting the processing chamber and the exhaust means, for causing a chemical reaction in a non-reacted gas and/or a by-product exhausted from the processing chamber, wherein the emission intensity of a plasma on the side of the exhaust means of the chemical reaction causing means is smaller than the emission intensity of a plasma on the side of the processing chamber.

40. (Original) The plasma processing process according to claim 39, wherein the atmosphere gas in the processing chamber is introduced into the chemical reaction causing means while maintaining a plasma state.

41. (Original) The plasma processing process according to claim 39, wherein extension of a plasma to the side of the exhaust means from the processing chamber is attenuated or inhibited by the chemical reaction causing means.

42. (Original) The plasma processing process according to claim 39, wherein the chemical reaction causing means comprises at least one of a reaction means by

a catalyst, a reaction means by a heated catalyst, and a reaction means by a heat generating member.

43. (Original) The plasma processing process according to claim 39, wherein the non-reacted gas and/or the by-product exhausted from the processing chamber comprises silicon.

44. (Original) The plasma processing process according to claim 39, wherein the plasma processing comprises at least one of film deposition, doping, etching, and H_2 plasma processing.

Claims 45-55 (Cancelled).